Sohya Kudoh

List of Publications by Year in descending order

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1937685 1720034 54 7 4 7 citations h-index g-index papers 7 7 7 14 docs citations times ranked citing authors all docs

#	Article	IF	CITATIONS
1	Variability Improvement by Si Surface Flattening of Electrical Characteristics in MOSFETs With High-k HfON Gate Insulator. IEEE Transactions on Semiconductor Manufacturing, 2015, 28, 266-271.	1.7	13
2	Improvement of Endurance Characteristics for Al-Gate Hf-Based MONOS Structures on Atomically Flat Si(100) Surface Realized by Annealing in Ar/H ₂ Ambient. IEICE Transactions on Electronics, 2018, E101.C, 328-333.	0.6	10
3	In situ formation of Hf-based metal/oxide/nitride/oxide/silicon structure for nonvolatile memory application. Japanese Journal of Applied Physics, 2018, 57, 114201.	1.5	10
4	Formation Mechanism of Atomically Flat Si(100) Surface by Annealing in Ar/H2 Ambient. Journal of Electronic Materials, 2018, 47, 961-965.	2.2	9
5	Improvement of Hf-based metal/oxide/nitride/oxide/Si nonvolatile memory characteristics by Si surface atomically flattening. Japanese Journal of Applied Physics, 2020, 59, SGGB10.	1.5	5
6	A Study on Si(100) Surface Flattening Utilizing Sacrificial Oxidation Process and Its Effect on MIS Diode Characteristics. IEICE Transactions on Electronics, 2015, E98.C, 402-405.	0.6	4
7	Reduction of process temperature for Si surface flattening utilizing Ar/H ₂ ambient annealing and its application to SOI-MISFETs with bilayer HfN high-k gate insulator. Japanese Journal of Applied Physics, 2020, 59, SCCB02.	1.5	3